L Number	Hits	Search Text	DB	Time stamp
2	5	(("6261876") or ("5970339") or ("5789305")	USPAT	2004/03/04 21:07
6	5071	or ("5494846") or ("5413953")).PN. ((438/149) or (438/311) or (438/423) or (438/425) or (438/426) or (438/443) or	USPAT; US-PGPUB;	2004/03/04 21:40
7	32097	(438/444) or (438/439) or (257/7) or (257/8) or (257/499) or (257/500) or (257/501) or (257/506)).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/03/04 21:42
0	70.00	trench or trenches	EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:42
8	78634	trench or trenches	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 21:42
9	373057	(insulate or insulating or insulation) near (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:43
10	2960	bulk near semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:43
12	6717	(soi or (semiconductor near2 insulator)) and (trench or trenches)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
13	3935	<pre>((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 21:44
14	3935	<pre>(((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
15	239		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
16		<pre>(((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor)) and (monolithic same intergrated)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:44
17	76883	monolithic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:45
19	4	((((((soi or (semiconductor near2 insulator)) and (trench or trenches)) and ((insulate or insulating or insulation) near (layer or film))) and ((insulate or insulating or insulation) near (layer or film))) and (bulk near semiconductor)) and monolithic) and (((438/149) or (438/311) or (438/423) or (438/425) or (438/426) or (438/443) or (438/444) or (438/439) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 21:45
		(257/7) or (257/8) or (257/499) or (257/500) or (257/501) or (257/506)).CCLS.)		

11	44	monolithic same intergrated	USPAT;	2004/03/04 21:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
18	28	(((((soi or (semiconductor near2 insulator))	USPAT;	2004/03/04 21:48
		and (trench or trenches)) and ((insulate or	US-PGPUB;	
		insulating or insulation) near (layer or	EPO; JPO;	
		film))) and ((insulate or insulating or	DERWENT;	
		insulation) near (layer or film))) and (bulk	IBM TDB	
		near semiconductor)) and monolithic	_	
-	1	("6613639").PN.	USPAT;	2003/11/02 14:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	